

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	353088	(heat or heated or heating or anneal or annealed or annealing) near8 (substrate wafer carrier holder)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 16:39
L2	11626	(form or forming or formed) near8 (Ru or Ruthenium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 16:39
L3	2214	L1 and L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 16:39
L4	708	L3 and ((oxidize or oxidizing or oxidized or oxidation) same (gas or precursor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 16:39
L5	3314	(Ru or Ruthenium) same (CVD or (chemical near vapor near deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 16:40
L6	293	4 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 16:41
L7	72615	(upper or lower or top or bottom or first or second) near8 (electrode or plate or metal) same capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 16:41
L8	155	6 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 16:51
L9	2	("6544834").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 17:28

EAST Search History

L10	11	(organoruthenium near8 precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 17:28
L11	4	("5314727" "6284655" "6316064" "6440495").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/07 17:32
L12	6	("20010006838" "20010023955" "5372849" "5834357" "6002036" "6110531").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/06/07 17:34
L13	490776	(increas\$4 or ramp-up or pre-heat\$4 or heat\$4 or anneal\$4 or thermal\$4) near8 (substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 17:55
L14	867373	(oxidize or oxidized or oxidizing or oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 17:56
L15	1254	14 same chamber same precursor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 17:56
L16	753	13 and 15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 17:57
L17	349	16 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 18:31
L19	2451	(ruthenium or Ru) near4 (gas\$3 or precursor\$3 or reactant\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 19:01
L20	341731	"O.sub.2" or "N.sub.2O" or "H.sub.2O" or "NO.sub.2" or "O.sub.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/07 19:01

EAST Search History

L21	986	L20 and L19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 19:50
L22	3706	(Ru or Ruthenium) near4 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 19:51
L23	246926	(heat\$4 or anneal\$4) near4 (substrate wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 19:51
L24	728692	capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 19:51
L25	796209	(bottom or lower) near4 (electrode plate capacitor metal conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 19:51
L26	306149	precursor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 19:51
L27	867373	(oxidize or oxidized or oxidizing or oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 19:51
L28	132	L22 and L23 and L24 and L25 and L26 and L27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 19:54